

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L21	87	FSG dual damascene and semiconductor substrate and polysilicon	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2010/06/11 13:25
L15	6	8 and 14	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 11:13
L14	96	(silica or (silicon near oxide) sio2 or "sio.sub.2") stress (dynes near "cm.sup.2")	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 11:13
L13	30	(dense or densified or densification) (teos or lto or \$4pecvd) (silica or (silicon near oxide) sio2 or "sio.sub.2") stress	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 11:06
L12	8	silicon rich pecvd (sio2 or "sio.sub.2") stress	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 11:04
L11	92	silicon rich pecvd (sio2 or "sio.sub.2")	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 11:02
L10	6	9 not 7	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 10:06
L9	9	5 and 8	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 10:06
L8	2223	((low\$2 with stress) same oxide) same2 ((high\$2 with stress) same oxide)	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 10:05
L7	7	5 and 6	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 10:00
L6	212	((low\$2 near stress) same oxide) and ((high\$2 near stress) same oxide)	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 10:00
L5	302	((silica or silicon near dioxide or "sio.sub.2" or sio2) cap\$4 (layer or coat\$4 or film)) same stress	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/11 10:00

L4	9092	(silica or silicon near dioxide or "sio.sub.2" or sio2) cap\$4 (layer or coat\$4 or film)	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/11 10:00
L3	20	1 not L2	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 09:34
L2	147	(low\$2 near stress) same oxide same (high\$2 near stress) same oxide	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 09:34
L1	167	((low\$2 near stress) same oxide) same2 ((high\$2 near stress) same oxide)	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/11 09:33
S147	147	(low\$2 near stress) same oxide same (high\$2 near stress) same oxide	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/10 17:12
S146	135	(low\$2 near stress) same oxide same (high\$2 near stress) same oxide	US-PGPUB; USPAT; USOCR	SAME	OFF	2010/06/10 17:12
S145	55	(low\$2 near stress) same oxide and (high \$2 near stress) same oxide and silicon with wafer	US-PGPUB; USPAT; USOCR	SAME	OFF	2010/06/10 17:08
S144	332	stress (pecvd or teos) oxide (low same high) and silicon with wafer	US-PGPUB; USPAT; USOCR	SAME	OFF	2010/06/10 17:04
S143	771	stress (pecvd or teos) oxide (low or high) and silicon with wafer	US-PGPUB; USPAT; USOCR	SAME	OFF	2010/06/10 17:04
S142	28	stress (pecvd or teos) oxide mpa and silicon with wafer	US-PGPUB; USPAT; USOCR	SAME	OFF	2010/06/10 17:01
S141	1	stress (pecvd or teos) oxide mpa and silicon with wafer	US-PGPUB; USPAT; USOCR	WITH	OFF	2010/06/10 17:00

S140	102	("2841510" "3370980" "3494809" "3632438" "3694276" "3723201" "3745423" "3862852" "3871007" "3900597" "3929529" "3997368").FN. OR ("4053335").URFN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/10 16:44
S139	30	S136 and epitax\$4 same wafer	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2010/06/10 16:43
S138	5	S136 and epitax\$2 same wafer	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2010/06/10 16:43
S137	29	S136 and epitaxial same wafer	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2010/06/10 16:42
S136	571	getter\$ (layer or coat \$4 or film) oxide protect\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2010/06/10 16:40
S135	80	S134 and stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 16:26
S134	329	S133 and oxide	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 16:26
S133	403	(polysilicon or polysi or (polycrystalline with (silicon or si))) same ((autodop\$4 or (auto near dop\$4)) or (outgas\$4 or (out near gas\$4)))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 16:26
S132	678	(polysilicon or polysi or (polycrystalline with (silicon or si))) and (autodop\$4 or (auto near dop\$4))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 16:26
S131	1176	(polysilicon or polysi or (polycrystalline with (silicon or si))) and autodop\$4 or auto near dop\$4	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 16:25

S130	64	stress (oxide or teos or LTO) (backside (back near side))	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/10 16:04
S129	3	stress (oxide or teos or LTO) (backside (back near side))	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/10 16:04
S128	0	dens\$4 (oxide or teos) (backside (back near side)) cap\$4 (film or coat\$4 or layer)	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/10 15:54
S127	102	("2841510" "3370980" "3494809" "3632438" "3694276" "3723201" "3745423" "3862852" "3871007" "3900597" "3929529" "3997368").FN. OR ("4053335").URFN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/10 15:53
S126	0	dens\$4 (oxide or teos) back side cap\$4 layer	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/10 15:52
S125	284	dens\$4 (oxide or teos) backside cap\$4 layer	US-PGPUB; USPAT; USOCR	SAME	ON	2010/06/10 15:52
S124	0	dens\$4 (oxide or teos) backside cap\$4 layer	US-PGPUB; USPAT; USOCR	WITH	ON	2010/06/10 15:52
S123	12	("4053335" "4687682" "5006202" "5201987" "5296385" "5562770" "5856230" "6017828" "6153536" "6180318").FN. OR ("6670283").URFN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/10 15:20
S122	47	S121 and getter\$4	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 15:15

S121	731	silicon with wafer and ((two or double) near5 (backside or (back near side)))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 15:14
S120	1917	silicon with wafer and ((two or double) with (backside or (back near side)))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 15:14
S119	37	(polysilicon or polysi or (polycrystalline with (silicon or si))) with getter\$4 and wafer and pecvd	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 15:11
S118	213	S117 and (backside or (back near side))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 14:47
S117	503	(polysilicon or polysi or (polycrystalline with (silicon or si))) with getter\$4 and wafer	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 14:46
S116	0	(polysilicon or polysi or (polycrystalline with (silicon or si))) with getter\$4 and wafer and lp-pecvd	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/10 14:45

EAST Search History (Interference)

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